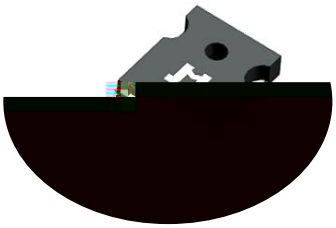
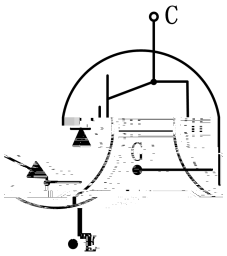
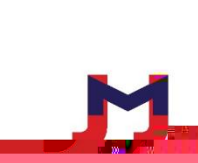
- V_{CE}=650V
- I_C=30A@T_C=100℃
- $V_{CE(sat)}$=1.7V(Typ.)

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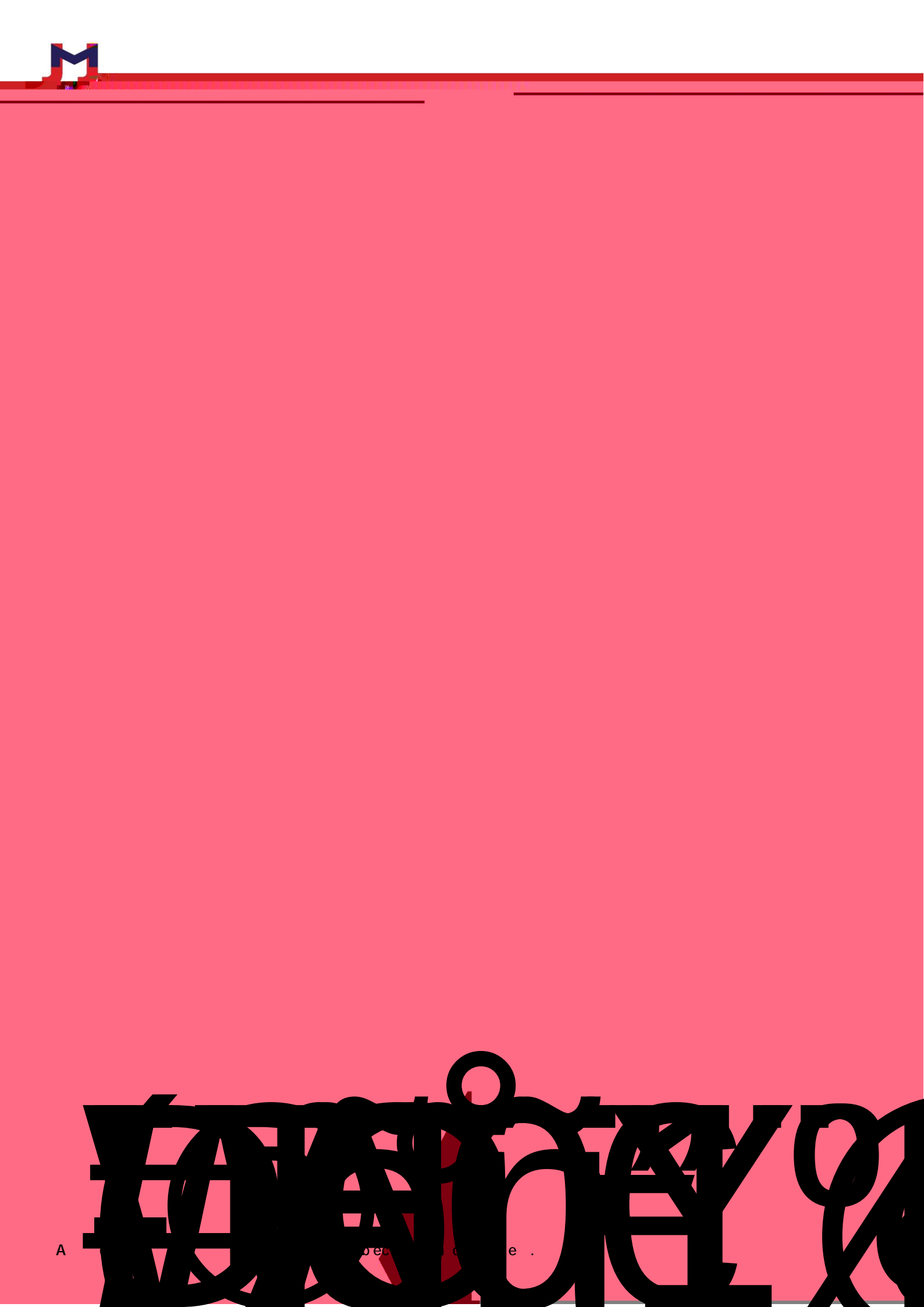
- High ruggedness performance.
- 10μs short circuim

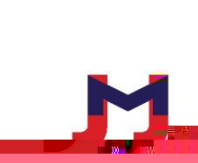


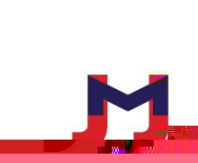


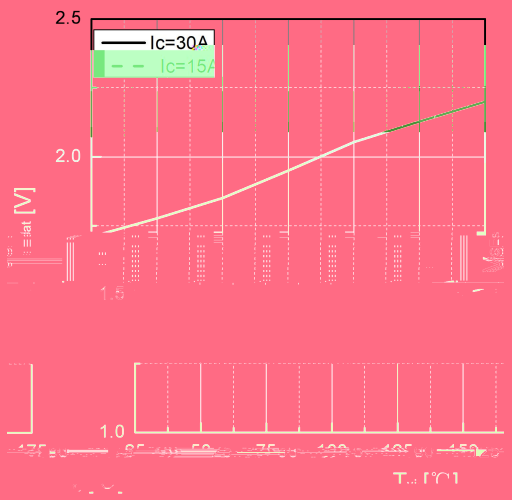
$_{CES}$	Collector-emitter breakdown voltage	$_{GE}$=0V, $_{C}$=250μA	650

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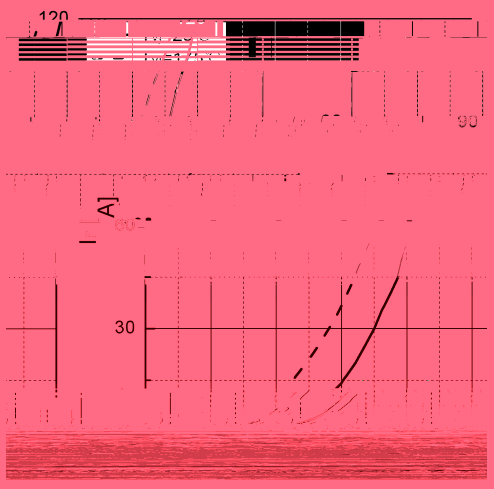


Fig 7. Typical $_{CEsat}$ as a function of $_{vj}$

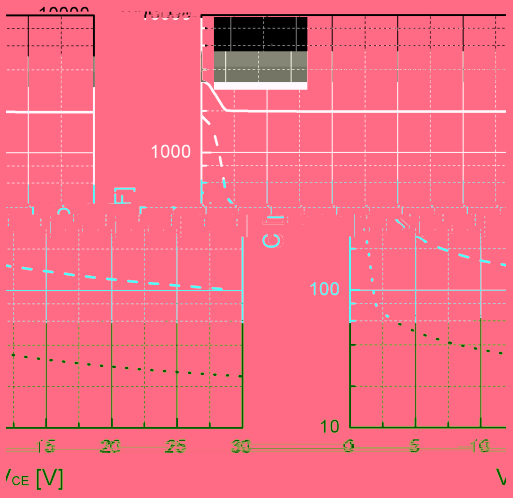


Fig 13. Typical capacitance as a function of $_{CE}$ (f=1Mhz, $_{GE}$=0V)

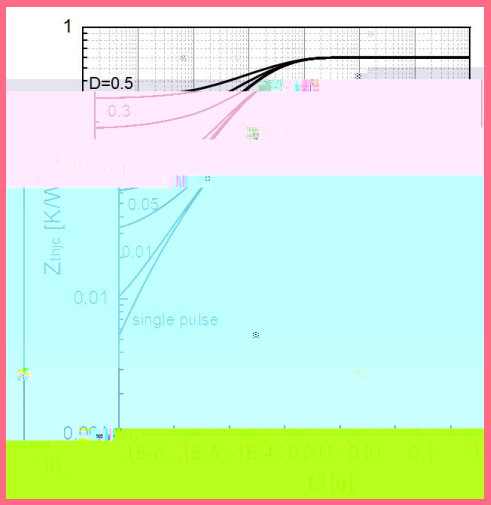
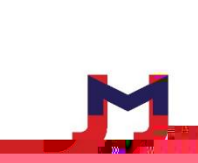


Fig 14. Transient thermal impedance of IGBT



Date	Revision	Changes
2024-03-20	Rev 1.1	Update
2024-05-17	Rev 1.2	Update
2025-03-09	Rev 1.3	Character update
2026-06-25	Rev 1.4	Update thermal

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